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Low Bond Line Film Adhesive High Flow, Electrically Insulating Thermally Conductive Ultra-Low Ionic Impurities Low Dielectric Constant (~3.66)

IDEAL FOR:

Electrically Insulating and Thermally Conductive
Die Attach Film Adhesive
High Temperature Laminate
Low Dielectric Loss Insulating Adhesive (<0.003)

DESCRIPTION:

ESP7665-HK is a die attach film adhesive that can also be applied to wafer level packaging. It contains a modified micro-alumina crystallite filled, highbond strength epoxy film designed for traditional die-attach application. It is also engineered and proven with outstanding stress absorbing capaility.

ESP7665-HK is a dry epoxy film that may be melt-laminated onto wafer or substrate of circuite sites at 100-130°C @ 5-15 psi without premature curing. It is also useful for bonding component and substrate to substrate and carrier with matched thermal coefficients of expansion. ESP7665-HK has good thermal conductivity to achieve one of the lowest thermal interface resistance.

AVAILABILITY:

ESP7665-HK is available in wafer, sheet sizes or as custom preforms. Standard thickness available is 25, 50 and 75 micron. Special thicknesses with tight tolerance are available.

APPLICATION PROCEDURES:

For Wafer Laminated Die-Attach:

- (1) Keep product at room temperature for 15 minutes. Remove film from protective paper.
- (2) Before using, remove protective liner from film.
- (3) Pre-laminate at 80-100°C @ <5 psi. Dice with standard tape and release procedure.
- (4) Place on heated substrate and cure*.

DIE-ATTACH FILM ESP7665-HK

TYPICAL PROPERTIES*

Electrical Resistivity >1x10 ¹⁴ ohm-cm

(150 °C/ 60 minutes)

Dielectric Strength (Volts/mil) > 750 Glass Transition Temp.(°C) 175 ±10%

Current Carrying Capabilities N/A Lap-Shear Strength N/A

Device Push-off Strength >4000 psi

>27.8 N/mm²

Hardness (Type) 90 (D) ±10% Cured Density (gm/cc) 2.2 ±10%

Thermal Conductivity >12.6 Btu-in/hr-ft²-°F ±10%

>1.8 W/m-°C ±10%

Linear Thermal Expansion 35 ±15%

Coeff. (ppm/°C)

Maximum Continuous Operation Temp. (°C) <150

*CURE SCHEDULES:

<u>Temperature</u>	<u>Time</u>	<u>Pressure</u>
100°C	2 hr	5-15 psi
125°C	1 hr	5-15 psi
150°C	30 min	3-15 psi

For tack-and-cure: Tack the die with DAF with heated collet and heated stage holding the header, leadframe, module or substrate at 100-150°C. Post curing at the same temperature.

Besides major transition of Tg at around 175°C, additional molecular relaxation occurs at 50-120°C.

SHELF LIFE:

Storage temperature

25°C

1 yr
in sealed package

<u>CAUTION:</u> This product may cause skin irritation. Avoid skin contact. If contact does occur, wash immediately with soap and water. Please refer SDS for more details.

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PRODUCT DATA SHEET Ver 2.0 4/2/2018

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